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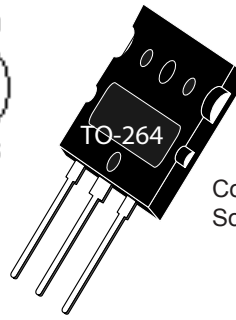
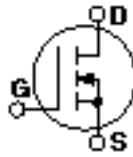
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Common Source

ARF469AG
ARF469BG

RF POWER MOSFETS

N-CHANNEL ENHANCEMENT MODE

150V 350W 45MHz

The ARF469A and ARF469B comprise a symmetric pair of common source RF power transistors designed for push-pull scientific, commercial, medical and industrial RF power amplifier applications up to 45 MHz. They have been optimized for both linear and high efficiency classes of operation.

- **Specified 150 Volt, 40.68 MHz Characteristics:**
 - Output Power = 350 Watts.**
 - Gain = 16dB (Class AB)**
 - Efficiency = 75% (Class C)**
- **Low Cost Common Source RF Package.**
- **Low V_{th} thermal coefficient.**
- **Low Thermal Resistance.**
- **Optimized SOA for Superior Ruggedness.**

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	Ratings	UNIT
V _{DSS}	Drain-Source Voltage	500	Volts
V _{DGO}	Drain-Gate Voltage	500	
I _D	Continuous Drain Current @ T _C = 25°C	30	Amps
V _{GS}	Gate-Source Voltage	±30	Volts
P _D	Total Power Dissipation @ T _C = 25°C	445	Watts
R _{θJC}	Junction to Case	0.28	°C/W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T _L	Lead Temperature: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage (V _{GS} = 0V, I _D = 250 μA)	500			Volts
R _{DS(ON)}	Drain-Source On-State Resistance ^① (V _{GS} = 10V, I _D = 15A)		0.25	0.28	ohms
I _{DSS}	Zero Gate Voltage Drain Current (V _{DS} = 500V, V _{GS} = 0V)			25	μA
	Zero Gate Voltage Drain Current (V _{DS} = 400V, V _{GS} = 0V, T _C = 125°C)			250	
I _{GSS}	Gate-Source Leakage Current (V _{GS} = ±30V, V _{DS} = 0V)			±100	nA
g _{fs}	Forward Transconductance (V _{DS} = 25V, I _D = 6.5A)		8		mhos
V _{GS(TH)}	Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1mA)	2		4	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Microsemi Website - <http://www.microsemi.com>

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 150V$ $f = 1\text{ MHz}$		2300		
C_{oss}	Output Capacitance			250		pF
C_{rss}	Reverse Transfer Capacitance			125		

FUNCTIONAL CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
G_{PS}	Common Source Amplifier Power Gain	$f = 40.68\text{ MHz}$	14	16		dB
η	Drain Efficiency	$V_{GS} = 2.5V$ $V_{DD} = 150V$	70	75		%
Ψ	Electrical Ruggedness VSWR 10:1	$P_{out} = 350W$	No Degradation in Output Power			

① Pulse Test: Pulse width < 380μS, Duty Cycle < 2%

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

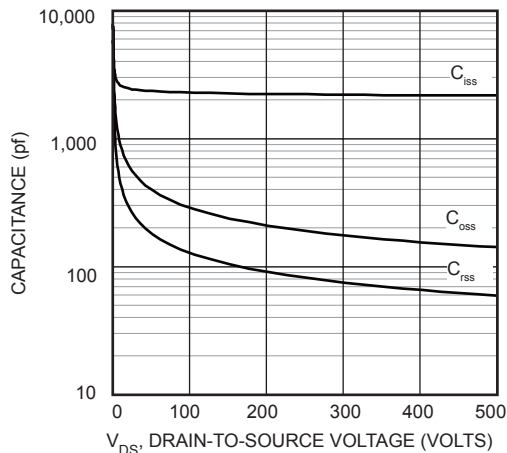


Figure 1, Typical Capacitance vs. Drain-to-Source Voltage

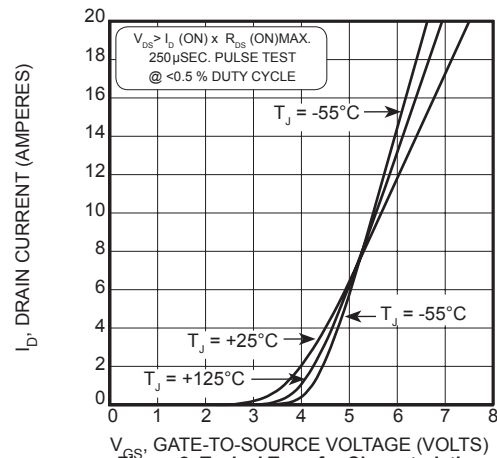


Figure 2, Typical Transfer Characteristics

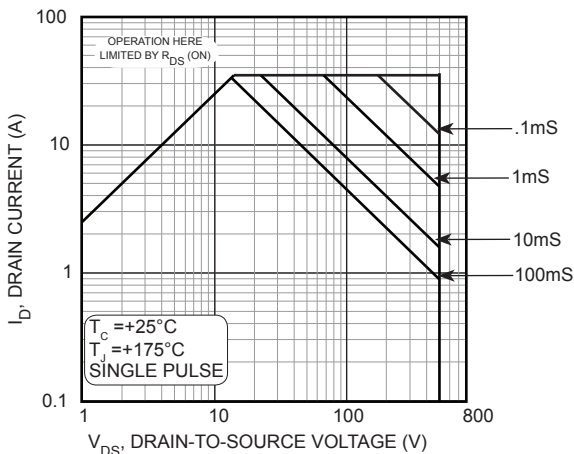


Figure 3, Typical Maximum Safe Operating Area

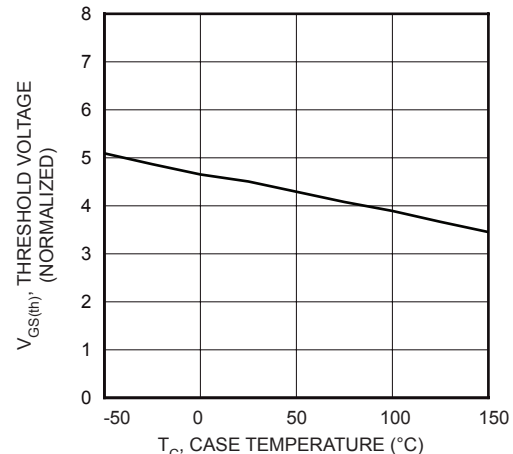


Figure 4, Typical Threshold Voltage vs Temperature

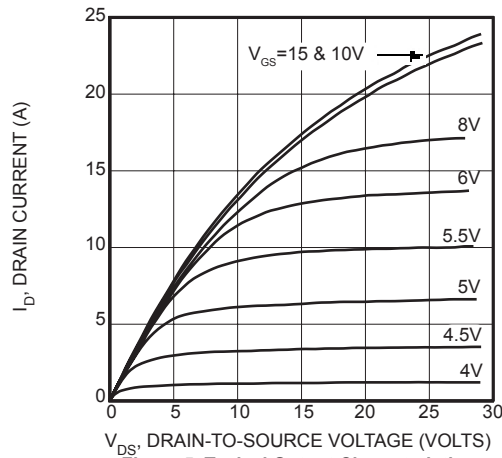


Figure 5, Typical Output Characteristics

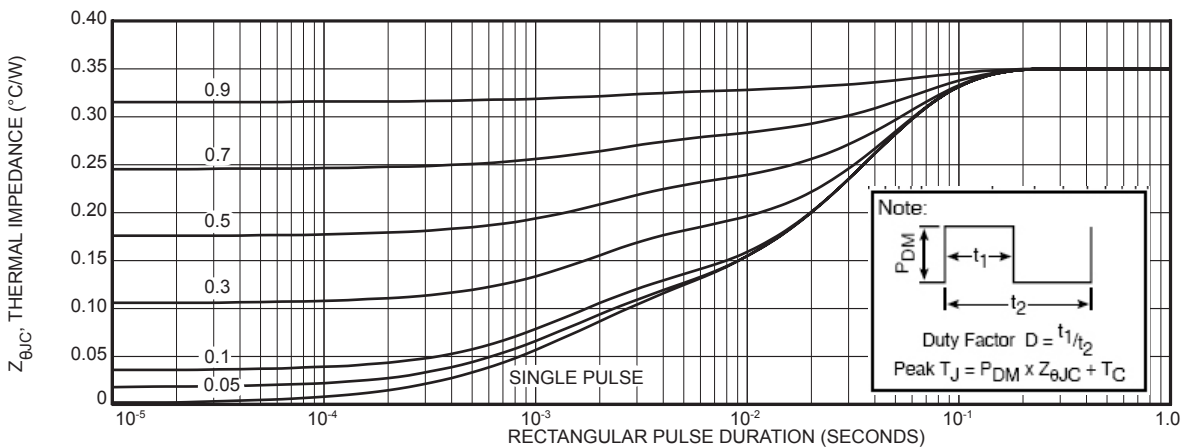


FIGURE 6a, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

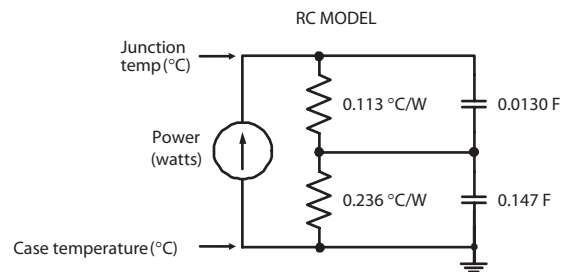
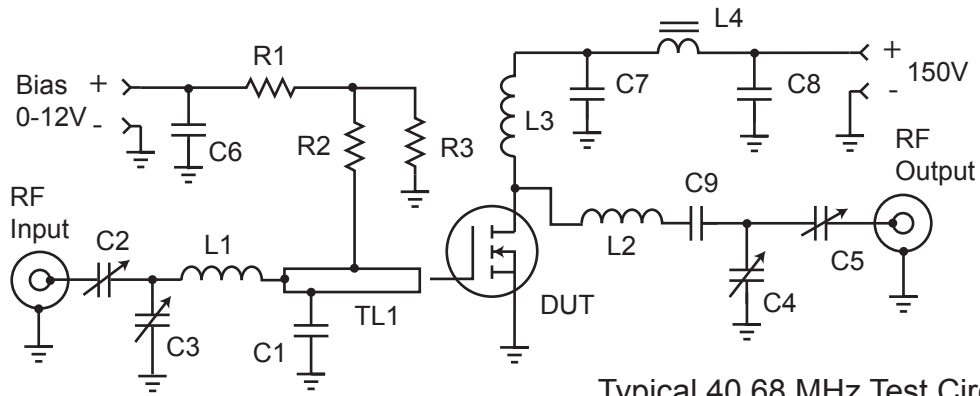


Figure 6b, TRANSIENT THERMAL IMPEDANCE MODEL

Table 1 - Typical Class AB Large Signal Input - Output Impedance

Freq. (MHz)	Z _{in} (Ω)	Z _{OL} (Ω)
2.0	18 - j 10.8	30 - j 1.5
13.5	1.3 - j 4.8	26 - j 9.6
27.1	0.4 - j 2.4	18 - j 13.1
40.7	0.2 - j 1.4	12 - j 12.4

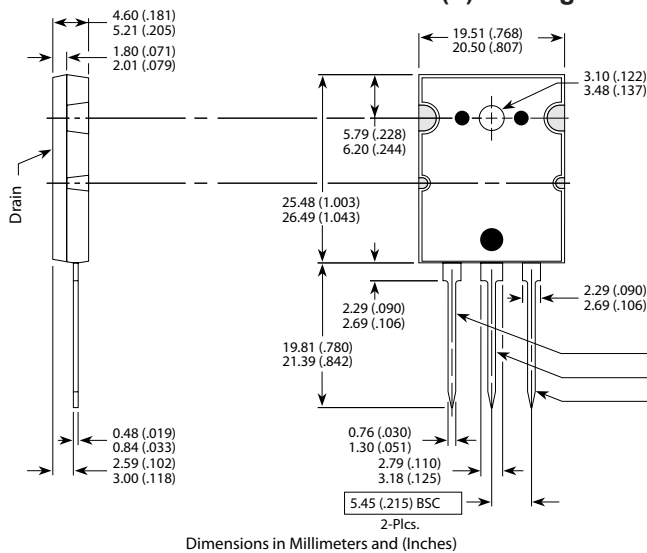
Z_{IN} - Gate shunted with 25Ω I_{dg} = 100mA
 Z_{OL} - Conjugate of optimum load for 300 Watts output at V_{dd}=150V



Typical 40.68 MHz Test Circuit

- | | | |
|----------------------------------|---|-------------------------------|
| C1 -- 2200pF ATC 700B | L1 -- 4t #22 AWG .25"ID .25" L ~87nH | R1- R3 -- 1kΩ 0.5Ω Carbon |
| C2-C5 -- Arco 465 Mica trimmer | L2 -- 5t #16 AWG .312" ID .35" L ~176nH | TL1 -- 34Ω t-line 0.175" x 1" |
| C6-C8 -- .1 μF 500V ceramic chip | L3 -- 10t #24 AWG .25"ID ~.5μH | C1 .45" from gate pin. |
| C9 -- 3x 2200 pF 500V chips COG | L4 -- VK200-4B ferrite choke 3μH | PCB -- 0.062" FR4, Er=4.7 |

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)
 NOTE: These two parts comprise a symmetric pair of RF power transistors and meet the same electrical specifications. The device pin-outs are the mirror image of each other to allow ease of use as a push-pull pair.

Device	
ARF - A	ARF - B
Gate	Drain
Source	Source
Drain	Gate

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